Data Sheet

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Manufacturers of World Class Discrete Semiconductors

CBR1-L010M SERIES
CBR2-L010M SERIES

SILICON BRIDGE RECTIFIER

CASE B-M

DESCRIPTION

The CENTRAL SEMICONDUCTOR CBR1-L010M, CBR2-L010M series types are silicon single phase full wave bridge rectifiers designed for general purpose applications.

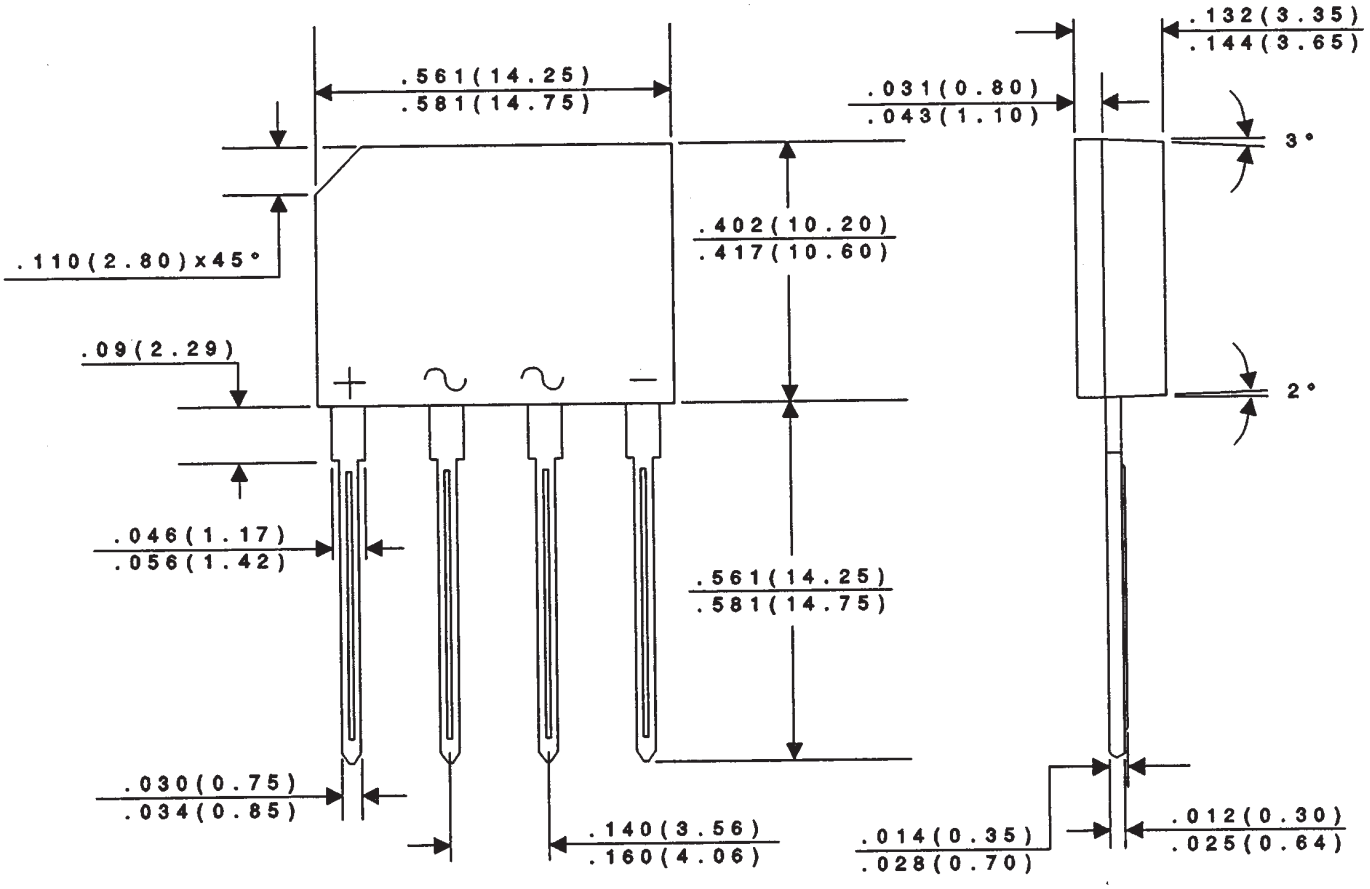
MAXIMUM RATINGS ($T_A = 25°C$ unless otherwise noted)

	SYMBOL	CBR1-L010M CBR2-L010M	CBR1-L020M CBR2-L020M	CBR1-L040M CBR2-L040M	CBR1-L060M CBR2-L060M	CBR1-L080M CBR2-L080M	CBR1-L100M CBR2-L100M	UNITS
Peak Repetitive Reverse Voltage	V_{RRM}	100	200	400	600	800	1000	V
DC Blocking Voltage	V_R	100	200	400	600	800	1000	V
RMS Reverse Voltage	$V_{R(RMS)}$	70	140	280	420	560	700	V
Average Forward Current ($T_A = 50°C$) (CBR1-L010M Series)	I_O			1.5				A
Average Forward Current ($T_A = 55°C$) (CBR2-L010M Series)	I_O			2.0				A
Peak Forward Surge Current (CBR1-L010M Series)	I_{FSM}			50				A
Peak Forward Surge Current (CBR2-L010M Series)	I_{FSM}			60				A
Operating and Storage Junction Temperature	T_J, T_{stg}			-65 to +150				°C

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
V_F	$I_F = 1.0A$ (CBR1-L010M Series)		1.0	V
V_F	$I_F = 2.0A$ (CBR2-L010M Series)		1.1	V
I_R	V_R = Rated V_{RRM}		10	μA
I_R	V_R = Rated V_{RRM}, $T_A = 125°C$		500	μA

CASE B-M - MECHANICAL OUTLINE



All Dimensions in Inches (mm).